# N-Channel 60-V (D-S) MOSFET

#### **Key Features:**

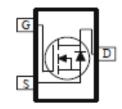
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
60	92 @ V <sub>GS</sub> = 10V	3.1	
	107 @ V <sub>GS</sub> = 4.5V	2.9	





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V <sub>DS</sub>	60	V		
Gate-Source Voltage		V <sub>GS</sub>	±20	v		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	1	3.1			
	T <sub>A</sub> =70°C	I <sub>D</sub>	2.5	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	15			
Continuous Source Current (Diode Conduction) <sup>a</sup>			1.9	А		
Dower Dissinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	1.3	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	١D	0.8	vv		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	100	°C/W	
	Steady State	ιν <sub>θ</sub> ja	166	C/VV	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

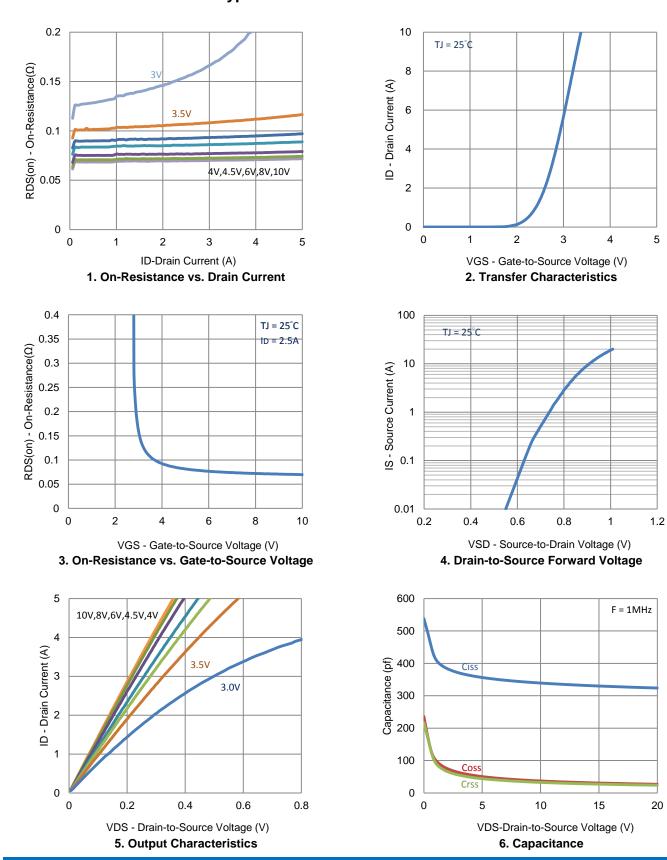
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
	DSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	5			А	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$			92	mΩ	
	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 2 \text{ A}$			107		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$		10		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 1 \text{ A}, V_{GS} = 0 \text{ V}$		0.74		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ $I_{D} = 2.5 \text{ A}$		4		nC	
Gate-Source Charge	Q <sub>gs</sub>			1.0			
Gate-Drain Charge	$Q_gd$	ID = 2.5 A		1.7			
Turn-On Delay Time	t <sub>d(on)</sub>	V = 20 V R = 12 0		3		ns	
Rise Time	t <sub>r</sub>	$V_{DS} = 30$ V, R <sub>L</sub> = 12 Ω, I <sub>D</sub> = 2.5 A, V <sub>GEN</sub> = 10 V, R <sub>GEN</sub> = 6 Ω		6			
Turn-Off Delay Time	t <sub>d(off)</sub>			17			
Fall Time	t <sub>f</sub>			5			
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		330		pF	
Output Capacitance	C <sub>oss</sub>			31			
Reverse Transfer Capacitance	C <sub>rss</sub>			27			

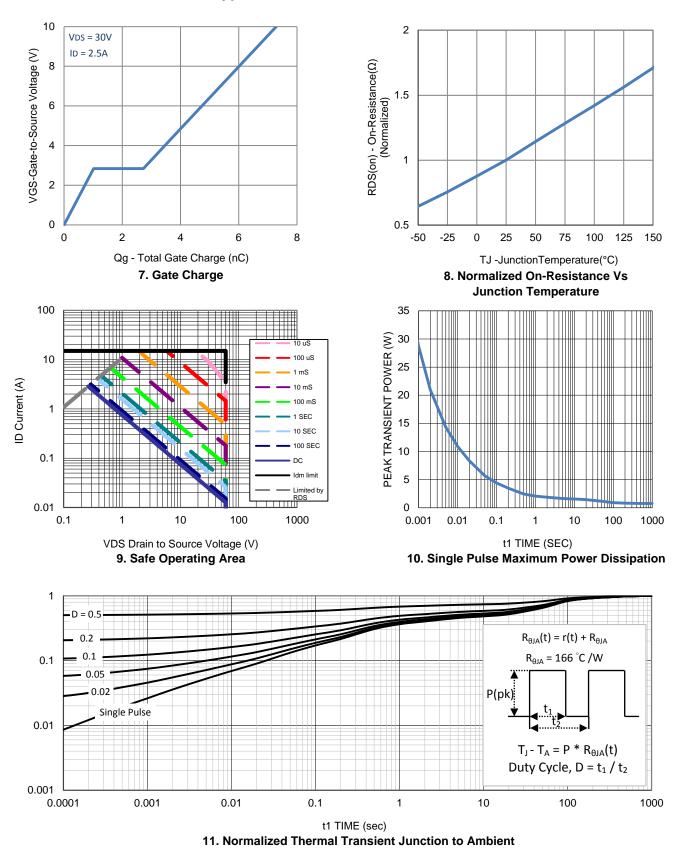
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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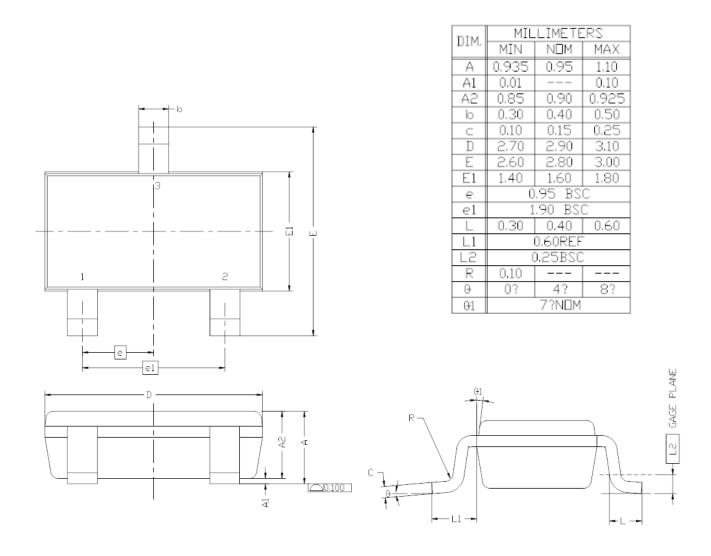


**Typical Electrical Characteristics** 



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### **Package Information**



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.